**Vishay Semiconductors** 

# Thyristor, Surface Mount, Phase Control SCR, 16 A



D<sup>2</sup>PAK

PRODUCT SUMMARY				
Package TO-263AB (D <sup>2</sup> PAK)				
Diode variation	Single SCR			
I <sub>T(AV)</sub>	16 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V			
V <sub>TM</sub>	1.25 V			
I <sub>GT</sub>	45 mA			
TJ	- 40 to 125 °C			

### **FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed qualified and according JEDEC-JESD47
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

### **APPLICATIONS**

- Input rectification (soft start)
- · Vishay input diodes, switches and output rectifiers which are available in identical package outlines

### DESCRIPTION

The VS-25TTS...SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	PLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE					
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 $\mu m$ ) copper	3.5	5.5				
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	A			
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0				

#### Note

•  $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$ 

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I <sub>T(AV)</sub>	Sinusoidal waveform	16	А			
I <sub>RMS</sub>		25	A			
V <sub>RRM</sub> /V <sub>DRM</sub>		800 to 1200	V			
I <sub>TSM</sub>		350	A			
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
TJ		- 40 to 125	°C			

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> ∕I <sub>DRM</sub> , AT 125 °C mA			
VS-25TTS08SPbF	800	800	10			
VS-25TTS12SPbF	1200	1200	10			







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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES		
FARAMETER	STNIDUL	STMBOL TEST CONDITIONS		TYP.	MAX.	UNITS	
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° c	conduction half sine wave	1	6		
Maximum RMS on-state current	I <sub>RMS</sub>			2	25	А	
Maximum peak, one-cycle,		10 ms sine pulse,	rated V <sub>RRM</sub> applied	3	00	A	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse,	no voltage reapplied	3	50		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse,	rated V <sub>RRM</sub> applied	450		A <sup>2</sup> s	
Maximum -t for fusing	141	10 ms sine pulse,	no voltage reapplied	630		A-5	
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 ms to 10 m	is, no voltage reapplied	63	800	A²√s	
Maximum on-state voltage drop	V <sub>TM</sub>	16 A, T <sub>J</sub> = 25 °C		1.	25	V	
On-state slope resistance	r <sub>t</sub>	T 105 %O		12	2.0	mΩ	
Threshold voltage	V <sub>T(TO)</sub>	1j = 125 C	T <sub>J</sub> = 125 °C		.0	V	
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	$V_{-}$ Deted $V_{-}$ $\Lambda/$	0	.5		
Maximum reverse and direct leakage current	IRM/IDM	$I_{RM}/I_{DM}$ $T_{J} = 125 \ ^{\circ}C$ $V_{R} = Rated V_{RRM}/V_{DRM}$		1	0		
Holding current	Ι <sub>Η</sub>	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C	-	150	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$		2	00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max., linear$	ar to 80 %, $V_{DRM} = R_g - k = Open$	5	00	V/µs	
Maximum rate of rise of turned-on current	dl/dt			1	50	A∕µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	А	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	60		
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45	mA	
		Anode supply = 6 V, resistive load, $T_J$ = 125 °C	20		
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	2.5		
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V	
Maximum DC gate voltage not to trigger	V <sub>GD</sub>				
Maximum DC gate current not to trigger	I <sub>GD</sub>	$T_{\rm J} = 125 ^{\circ}\text{C},  V_{\text{DRM}} = \text{Rated value}$ 2.		mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9		
Typical reverse recovery time	t <sub>rr</sub>	T 105 %C	4	μs	
Typical turn-off time	tq	T <sub>J</sub> = 125 °C	110		

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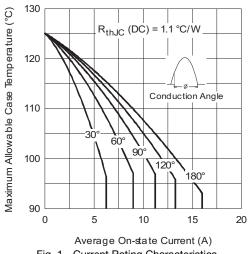
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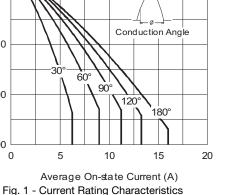
THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C	
Soldering temperature	Τ <sub>S</sub>	For 10 s (1.6 mm from case)	260		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.1	°C/W	
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> <sup>(1)</sup>		40	0/11	
Approximate weight			2	g	
Approximate weight			0.07	oz.	
Marking device		Case style D <sup>2</sup> PAK (SMD-220)	25TT	S08S	
		Case signe D-FAR (SIVID-220)	25TT	S12S	

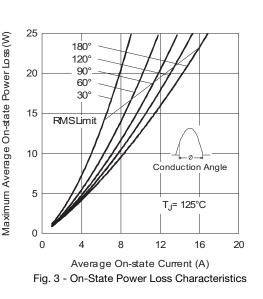
#### Note

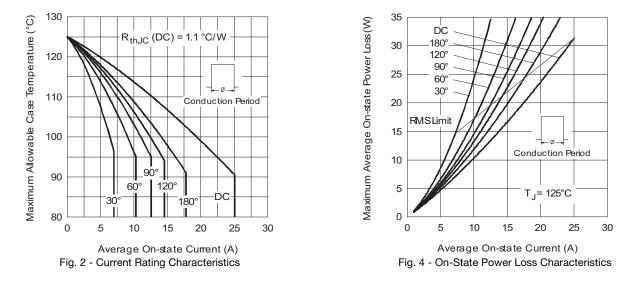
(1) When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W

For recommended footprint and soldering techniques refer to application note #AN-994







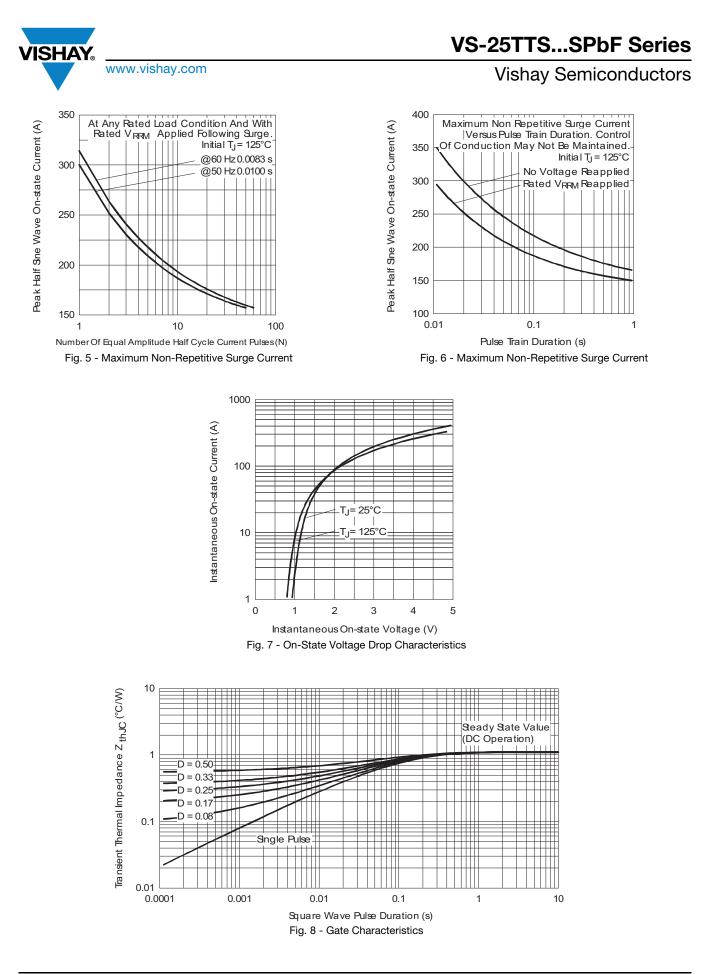


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## VS-25TTS...SPbF Series

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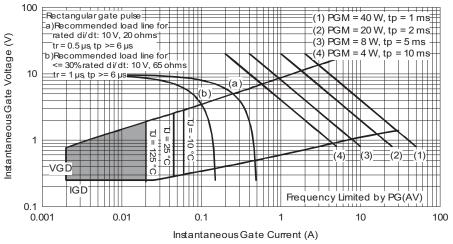


Fig. 9 - Thermal Impedance ZthJC Characteristics

### **ORDERING INFORMATION TABLE**

www.vishay.com

Device code	VS-	25	т	т	S	12	S	TRL	PbF	
	1	2	3	4	5	6	7	8	9	
	1 -	- Visl	nay Sen	niconduc	ctors pro	oduct				
	2 -	- Cur	rent rati	ng (25 =	= 25 A)					
	3 -		uit conf Single t	iguratior hyristor	ו:					
	4 -		kage: TO-220	AC						
	5 -	- Тур	e of silio		erv rect	ifier			08 = 8	800 V
	6 -			ng: Volt			) = V <sub>RRI</sub>	M		200 V
	7 -	- S =	TO-220	) D <sup>2</sup> PAK	(SMD-	220) ve	rsion			
	8 -	• TF		ube be and re pe and r			,			
	9 -	· PbF	= Leac	l (Pb)-fre	ee					

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-25TTS08SPbF	50	1000	Antistatic plastic tubes				
VS-25TTS08STRRPbF	800	800	13" diameter reel				
VS-25TTS08STRLPbF	800	800	13" diameter reel				
VS-25TTS12SPbF	50	1000	Antistatic plastic tubes				
VS-25TTS12STRRPbF	800	800	13" diameter reel				
VS-25TTS12STRLPbF	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95046				
Part marking information	www.vishay.com/doc?95054			
Packaging information	www.vishay.com/doc?95032			

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## **Outline Dimensions**

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D<sup>2</sup>PAK



Conforms to JEDEC outline D<sup>2</sup>PAK (SMD-220) в Pad layout (2)(3)A 11.00 MIN.-(E) F (0.43)ŧ (3) L1 4 ( |(0.38)<sup>MIN.</sup> (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З 0.15)<sup>0.01</sup> Ľ L2 Ĥ ţ В В 2.32 MIN. (0.08) 2.64 (0.103) 2.41 (0.096) (3)Г 2 x b2 С View A - A 2 x h // ± 0.004 M B ⊕ 0.010 M A M B Base Plating (4) Metal 2 x e Н b1, b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 A1 Lead tip (b, b2) Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A" 3. - Anode

Rotated 90 °CW Scale: 8:1

SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES	STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

#### Notes

 $^{(1)}\,$  Dimensioning and tolerancing per ASME Y14.5 M-1994  $\,$ 

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC outline TO-263AB

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### **DIMENSIONS** in millimeters and inches



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